

General Description

The WST2337A is the highest performance trench P-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the small power switching and load switch applications.

The WST2337A meet the RoHS and Green Product requirement with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

Product Summery

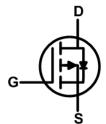
BVDSS	RDSON	ID
-15V	30mΩ	-4.8A

Applications

- High Frequency Point-of-Load Synchronous
 Small power switching for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

SOT-23-3L Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units	
V_{DS}	Drain-Source Voltage	-15	V	
V_{GS}	Gate-Source Voltage	±12	V	
I _D @T _c =25℃	Continuous Drain Current, V _{GS} @ -4.5V ¹ -4.8			
I _D @T _c =70°C	Continuous Drain Current, V _{GS} @ -4.5V ¹	-3.4	А	
I _{DM}	Pulsed Drain Current	-24	А	
P _D @T _A =25℃	Total Power Dissipation ³	1.4	W	
T _{STG}	Storage Temperature Range -55 to 150		$^{\circ}$	
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}$	

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient ¹		125	°C/W
$R_{ heta JC}$	Thermal Resistance Junction-Case ¹		80	°C/W



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-15			V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-4.5V , I _D =-4.1A		30	48	mΩ
T (DS(ON)		V_{GS} =-2.5V , I_D =-3A		45	65	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250uA$	-0.45	-0.7	-1.2	V
I _{DSS}	Drain-Source Leakage Current	V_{DS} =-12V , V_{GS} =0V , T_{J} =25 $^{\circ}$ C			-1	uA
I _{GSS}	Gate-Source Leakage Current	V_{GS} = $\pm 12V$, V_{DS} = $0V$			±100	nA
Qg	Total Gate Charge			7.8		nC
Q_{gs}	Gate-Source Charge	V _{DS} =-4V,I _D =-4.1A,V _{GS} =-4.5V		1.2		
Q_{gd}	Gate-Drain Charge			1.6		
T _{d(on)}	Turn-On Delay Time	V_{DD} =-4V, I_{D} =-3.3A , R_{L} =-1.2 Ω , V_{GEN} =-4.5V, R_{g} =1 Ω		12		
Tr	Rise Time			35		
T _{d(off)}	Turn-Off Delay Time			30		ns
T _f	Fall Time			10		.
C _{iss}	Input Capacitance	V _{DS} =-4V,V _{GS} =0V,		738	1500	
C _{oss}	Output Capacitance	F=1.0MHz		280		pF
C _{rss}	Reverse Transfer Capacitance	I'- I.UIVIITZ		190		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current	V _G =V _D =0V , Force Current			-4.1	Α
V_{SD}	Diode Forward Voltage	V_{GS} =0V , I_{S} =-1.6A , T_{J} =25 $^{\circ}$ C			-1.2	V

Notes:

- $\textbf{1.} \ \ \textbf{Repetitive Rating: Pulse width limited by maximum junction temperature.}$
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production



Typical Characteristics

Figure 1:Switching Test Circuit

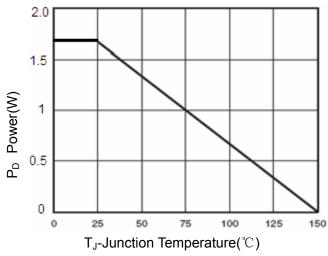


Figure 3 Power Dissipation

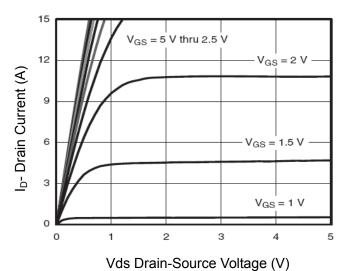


Figure 5 Output Characteristics

Figure 2:Switching Waveforms

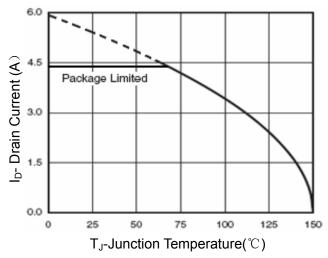


Figure 4 Drain Current

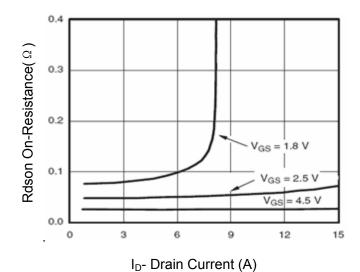
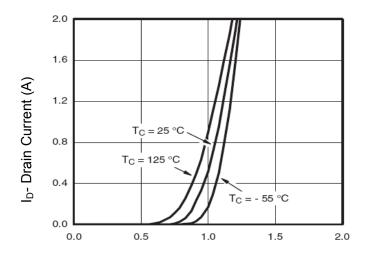
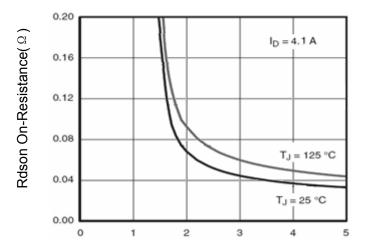


Figure 6 Drain-Source On-Resistance





Vgs Gate-Source Voltage (V)
Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V) Figure 9 Rdson vs Vgs

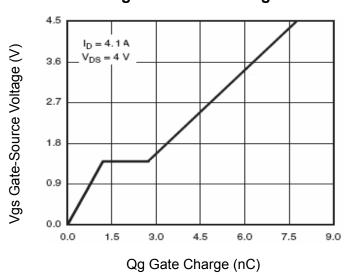


Figure 11 Gate Charge

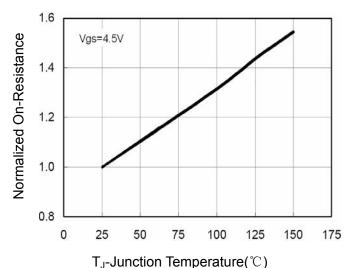
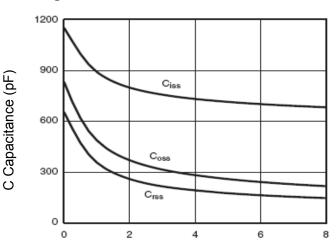
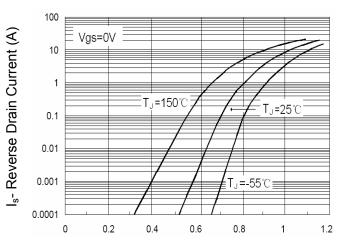


Figure 8 Drain-Source On-Resistance



Vds Drain-Source Voltage (V)

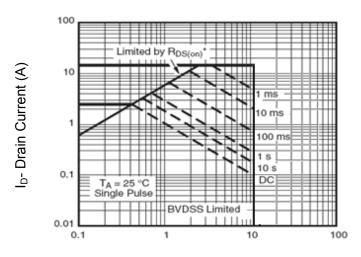
Figure 10 Capacitance vs Vds



Vsd Source-Drain Voltage (V)

Figure 12 Source- Drain Diode Forward





Vds Drain-Source Voltage (V)

Figure 13 Safe Operation Area

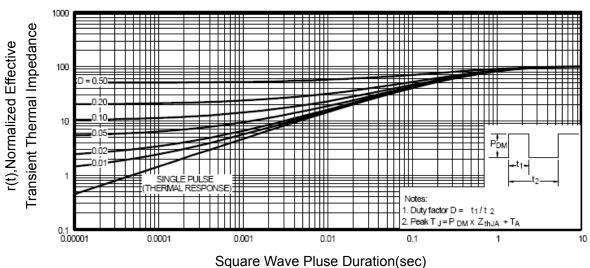


Figure 14 Normalized Maximum Transient Thermal Impedance



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